

Medium Power Transistor (32V, 0.8A) 2SD1781K

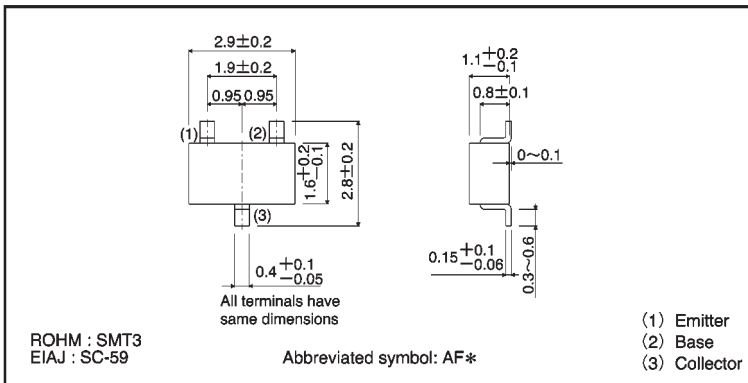
●Features

- 1) Very low $V_{CE(sat)}$.
 $V_{CE(sat)} < 0.4 \text{ V (Typ.)}$
($I_C / I_B = 500\text{mA} / 50\text{mA}$)
- 2) High current capacity in compact package.
- 3) Complements the 2SB1197K..

● Structure

Epitaxial planar type
NPN silicon transistor

● External dimensions (Units: mm)



* Denotes h_{FE}

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	32	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	0.8	A (DC)
		1.5	A (Pulse) *
Collector power dissipation	P_C	200	mW
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55~+150	°C

* Single pulse $P_w=100\text{ms}$

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	40	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	32	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB}=20V$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.4	V	$I_C/I_B=500mA/50mA$
DC current transfer ratio	h_{FE}	120	—	390	—	$V_{CE}=3V, I_C=100mA$
Transition frequency	f_T	—	150	—	MHz	$V_{CE}=5V, I_E=-50mA, f=100MHz$
Output capacitance	C_{ob}	—	10	—	pF	$V_{CB}=10V, I_E=0A, f=1MHz$

●Packaging specifications and h_{FE}

Type	h_{FE}	Package	Taping
		Code	T146
		Basic ordering unit (pieces)	3000
2SD1781K	QR		○

h_{FE} values are classified as follows :

Item	Q	R
h_{FE}	120~270	180~390

●Electrical characteristic curves

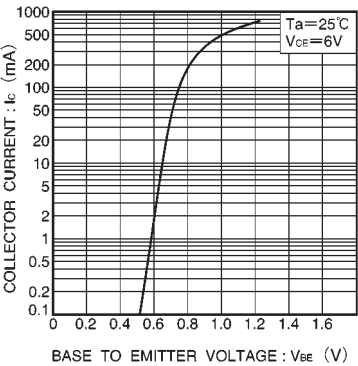


Fig.1 Grounded emitter propagation characteristics

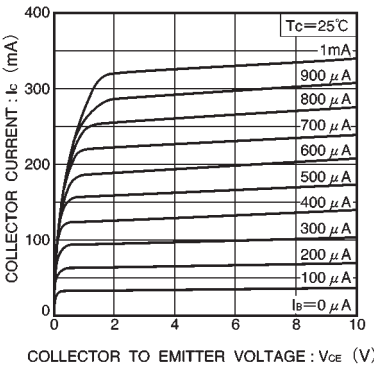


Fig.2 Grounded emitter output characteristics

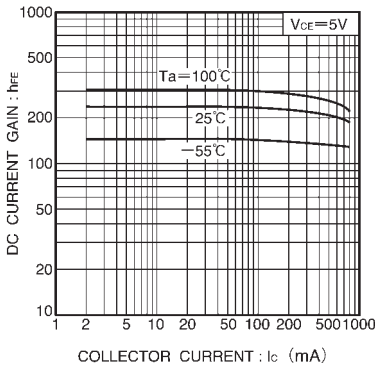


Fig.3 DC current gain vs. collector current

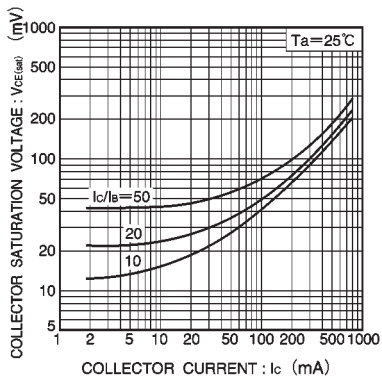


Fig.4 Collector-emitter saturation voltage vs. collector current (I)

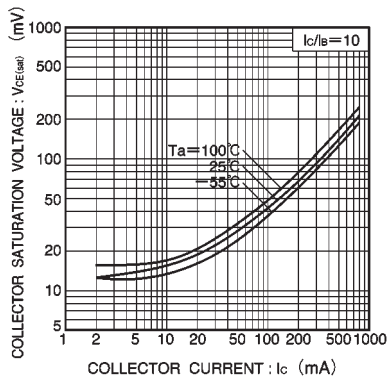


Fig.5 Collector-emitter saturation voltage vs. collector current (II)

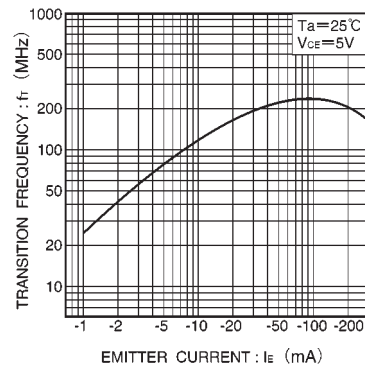


Fig.6 Gain bandwidth product vs. emitter current

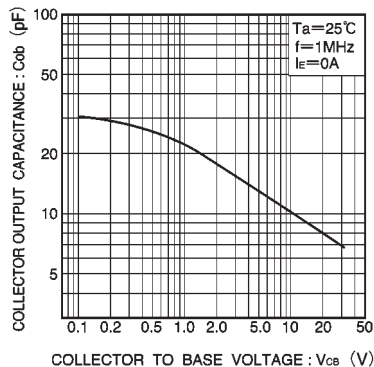


Fig.7 Collector output capacitance vs. collector-base voltage

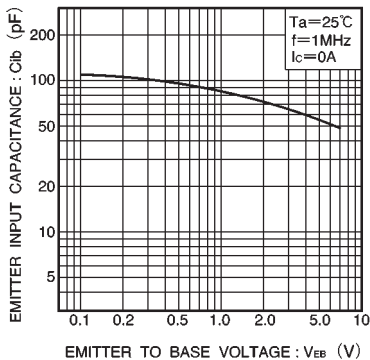


Fig.8 Emitter input capacitance vs. emitter-base voltage